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Properties of ZrO₂; 4.6 Hafnium Dioxide; 4.6.1 Processes and Properties of HfO₂; 4.7 Other Oxides; 4.7.1 Tin Oxide 4.7.2 Indium Oxide 4.7.3 Tantalum Oxide; 4.8 Mixed Oxides and Nanolaminates; 4.8.1 Mixed Oxide Processes; 4.8.2 Nanolaminate Oxides; 4.9 Multilayers; References; 5 Nitrides and Other Compounds; 5.1 Introduction; 5.2 Nitrides; 5.2.1 Transition Metal Nitrides; 5.2.2 Group III Nitrides; 5.2.3 Group IV Nitrides; 5.2.4 Mixed Nitrides; 5.3 Chalcogenides; 5.4 Other Compounds; References; 6 Metals; 6.1 Introduction; 6.2 Noble Metals; 6.2.1 Silver Processes and Applications; 6.2.2 Ruthenium Processes and Applications; 6.2.3 Platinum and Palladium Processes and Applications 6.2.4 Rhodium Processes and Applications 6.2.5 Iridium Processes and Applications; 6.3 Titanium; 6.4 Tantalum; 6.5 Aluminum; 6.6 Copper; 6.7 Other Transition Metals; References; 7 Organic and Hybrid Materials; 7.1 Introduction; 7.2 Organic layers; 7.3 Hybrid Organic-inorganic Layers.; 7.4 Applications of Organic and Hybrid Films; References; 8 ALD Applications and Industry; 8.1 Introduction; 8.2 MEMS/NEMS; 8.3 Thin Film Magnetic Heads; 8.4 Coating Nanoparticles, Nanomaterials and Porous Objects; 8.5 Optical Coatings; 8.6 Thin Film Electroluminescent Displays; 8.7 Solar Cells 8.8 Anti-corrosion Layers 8.9 Opportunities in Organic Electronics; 8.10 ALD Tool Manufacturers and Coating Providers; References; Index

Sommario/riassunto

Since the first edition was published in 2008, Atomic Layer Deposition (ALD) has emerged as a powerful, and sometimes preferred, deposition technology. The new edition of this groundbreaking monograph is the first text to review the subject of ALD comprehensively from a practical perspective. It covers ALD's application to microelectronics (MEMS) and nanotechnology; many important new and emerging applications; thermal processes for ALD growth of nanometer thick films of semiconductors, oxides, metals and nitrides; and the formation of organic and hybrid materials.
